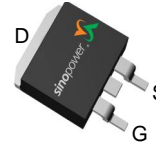


N-Channel Enhancement Mode MOSFET

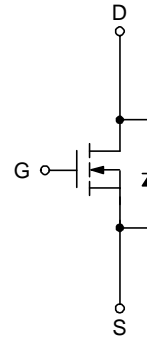
Features

- 40V/120A,
 $R_{DS(ON)} = 1.7m\Omega(max.) @ V_{GS} = 10V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- 100% UIS + R_g Tested

Pin Description



Top View of TO-263-3



N-Channel MOSFET

Applications

- High Efficiency Synchronous Rectification in SMPS.
- Uninterruptible Power Supply.
- High Speed Power Switching.

Ordering and Marking Information

<p>SM4020NH □□-□□□</p> <ul style="list-style-type: none"> □□ □ Assembly Material □□ □ Handling Code □□ □ Temperature Range □□ □ Package Code 	<p>Package Code G : TO-263-3 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel (800ea/reel) Assembly Material G : Halogen and Lead Free Device</p>
<p>SM4020NH G : SM4020NH XXXXX</p>	<p>XXXXX - Lot Code</p>

Note: SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
Common Ratings			
V_{DSS}	Drain-Source Voltage	40	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 120 ^a	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 120 ^a	
		$T_C=100^\circ\text{C}$ 120	
I_{DM}	Pulsed Drain Current	$T_C=25^\circ\text{C}$ 400 ^b	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 250	W
		$T_C=100^\circ\text{C}$ 100	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State 0.5	$^\circ\text{C}/\text{W}$
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$ 29	A
		$T_A=70^\circ\text{C}$ 23.5	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 2.5	W
		$T_A=70^\circ\text{C}$ 1.6	
$R_{\theta JA}$ ^c	Thermal Resistance-Junction to Ambient	Steady State 50	$^\circ\text{C}/\text{W}$
I_{AS} ^d	Avalanche Current, Single pulse	$L=0.5\text{mH}$ 60	A
E_{AS} ^d	Avalanche Energy, Single pulse	$L=0.5\text{mH}$ 900	mJ

Note a : I_D max. current limited by bond wire.

Note b : Pulse width limited by max. junction temperature.

Note c : Surface Mounted on 1in^2 pad area, $t=999\text{s}$.

Note d : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

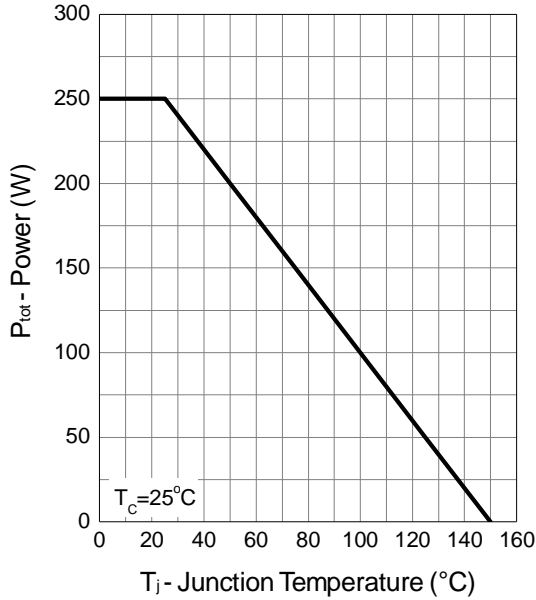
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=32V, V_{GS}=0V$ $T_J=85^\circ\text{C}$	-	-	1	μA
			-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
$R_{DS(ON)}^e$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=40A$	-	1.4	1.7	$m\Omega$
Diode Characteristics						
V_{SD}^e	Diode Forward Voltage	$I_{SD}=20A, V_{GS}=0V$	-	0.76	1.1	V
t_{rr}	Reverse Recovery Time	$I_{SD}=40A, dI_{SD}/dt=100A/\mu s$	-	71.6	-	ns
Q_{rr}	Reverse Recovery Charge		-	71.9	-	nC
Dynamic Characteristics ^f						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$	-	0.8	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=20V,$ Frequency=1.0MHz	-	10555	13721	μF
C_{oss}	Output Capacitance		-	3900	-	
C_{riss}	Reverse Transfer Capacitance		-	235	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=20V, R_L=20\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=1\Omega$	-	41	75	ns
t_r	Turn-on Rise Time		-	21	39	
$t_{d(OFF)}$	Turn-off Delay Time		-	84	152	
t_f	Turn-off Fall Time		-	111	201	
Gate Charge Characteristics ^f						
Q_g	Total Gate Charge	$V_{DS}=20V, V_{GS}=10V,$ $I_{DS}=40A$	-	178	249	nC
Q_{gs}	Gate-Source Charge		-	52	-	
Q_{gd}	Gate-Drain Charge		-	32	-	

Note e : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

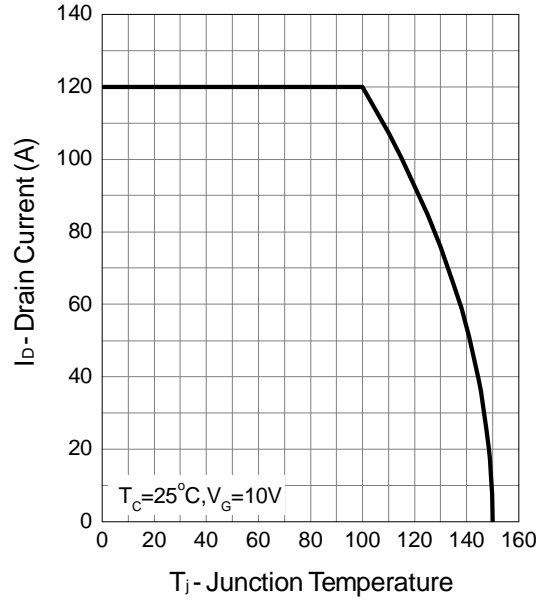
Note f : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

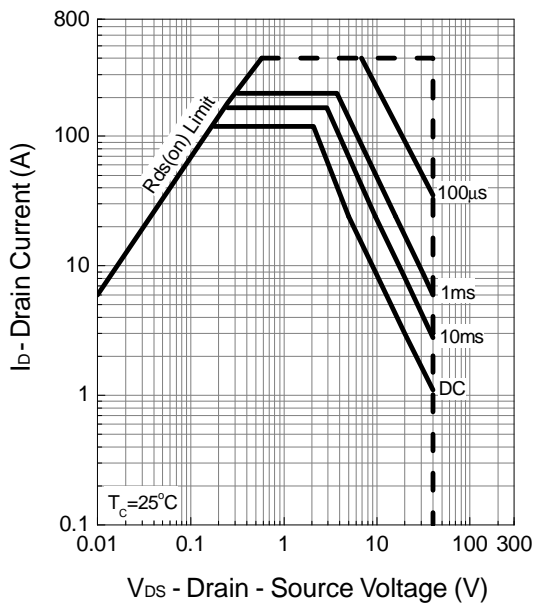
Power Dissipation



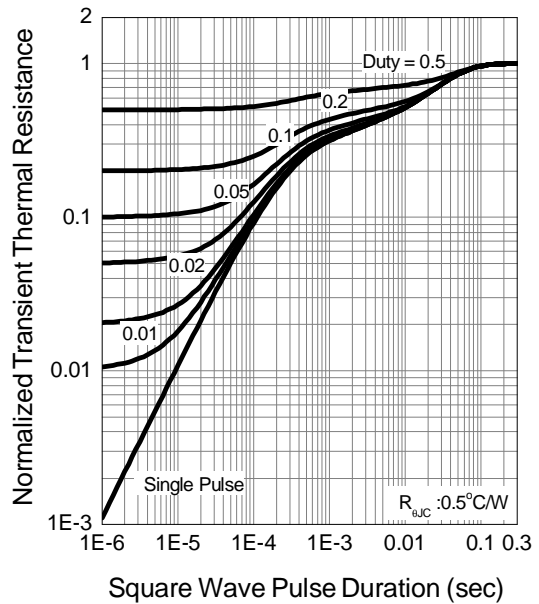
Drain Current



Safe Operation Area

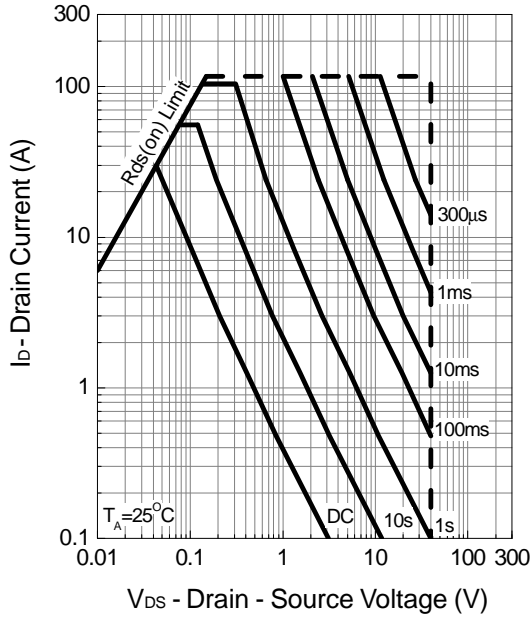


Thermal Transient Impedance

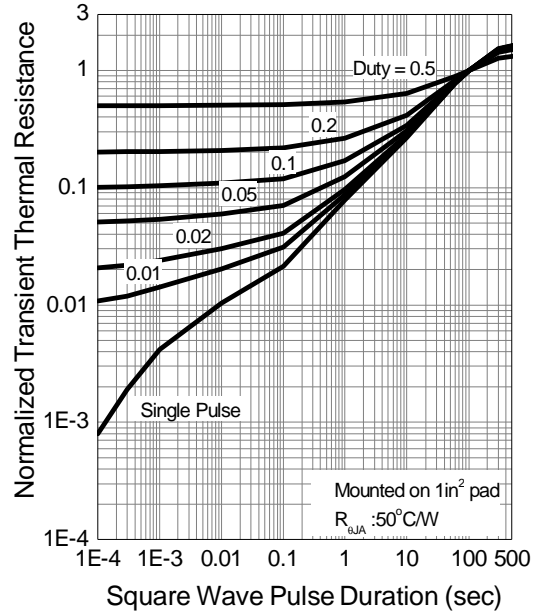


Typical Operating Characteristics (Cont.)

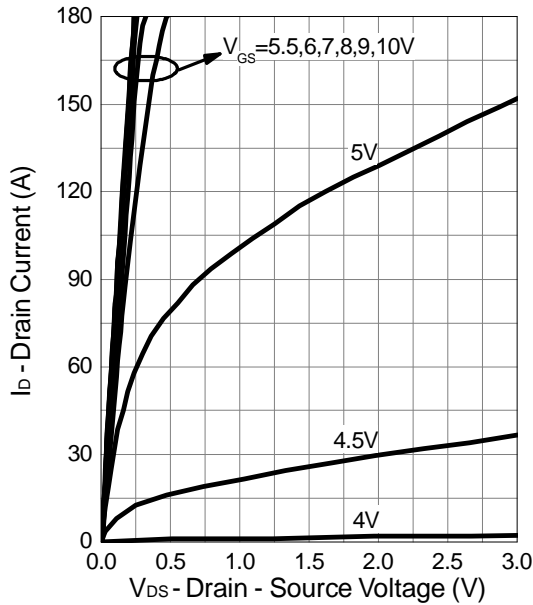
Safe Operation Area



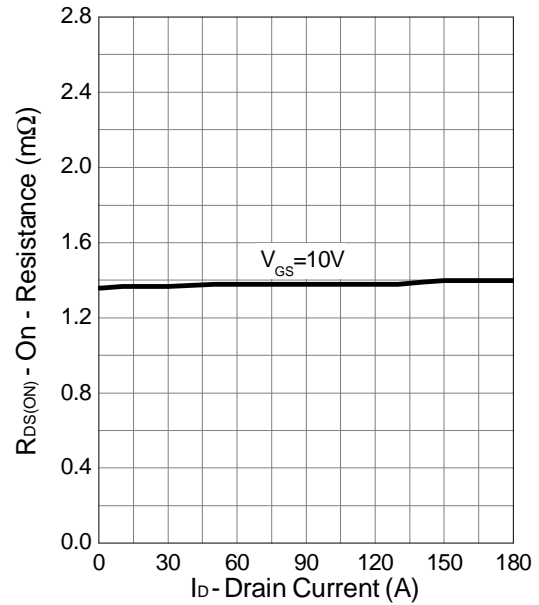
Thermal Transient Impedance



Output Characteristics

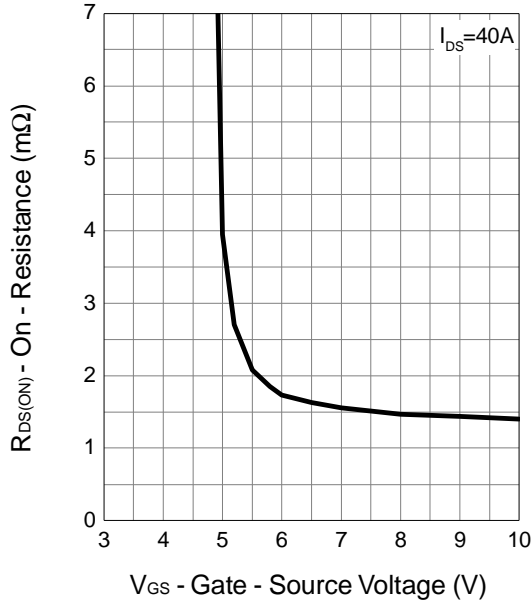


Drain-Source On Resistance

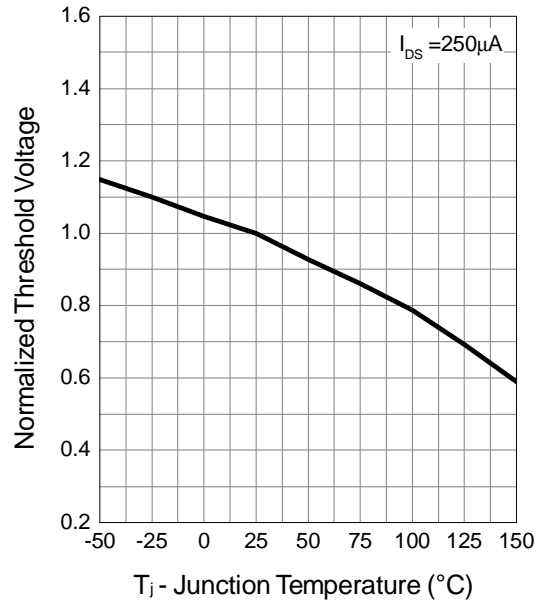


Typical Operating Characteristics (Cont.)

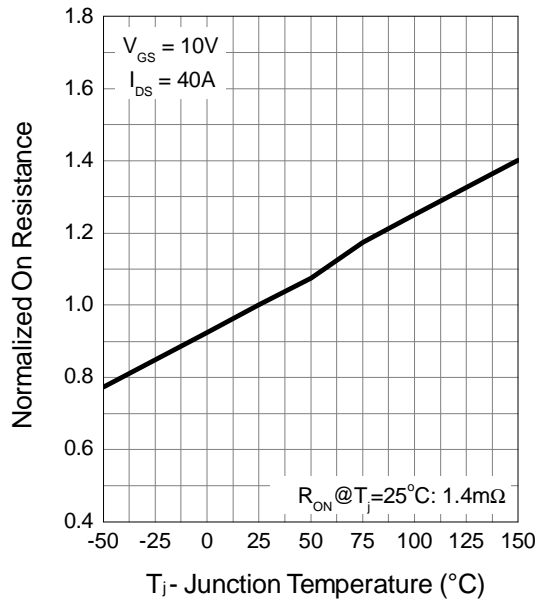
Gate-Source On Resistance



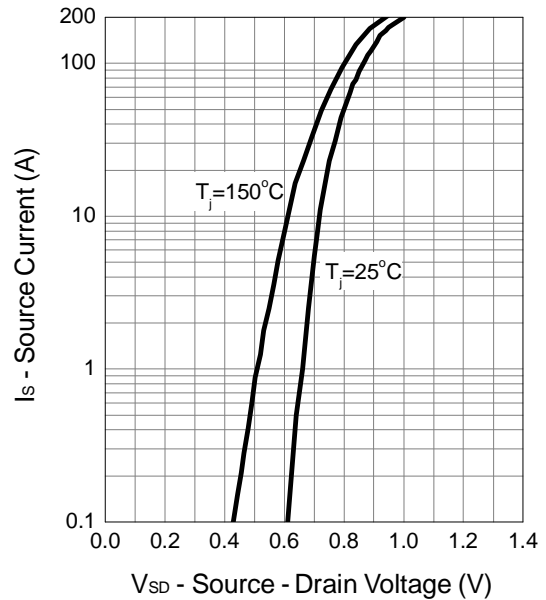
Gate Threshold Voltage



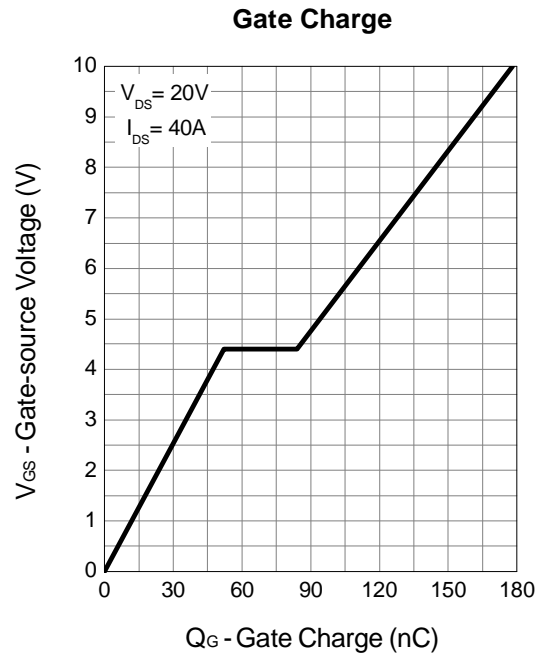
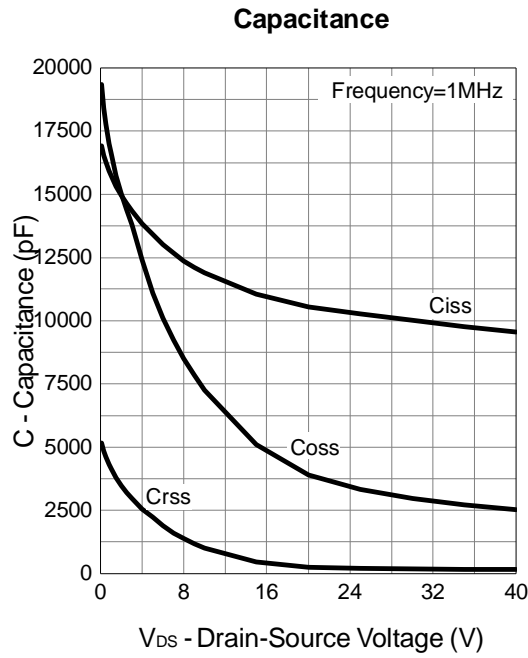
Drain-Source On Resistance



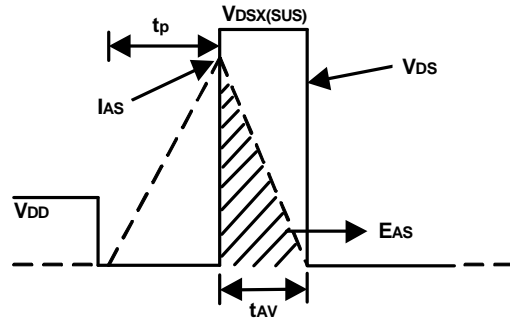
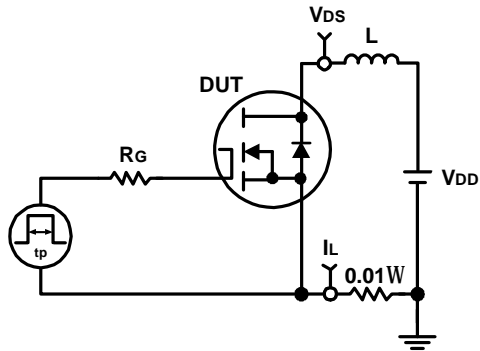
Source-Drain Diode Forward



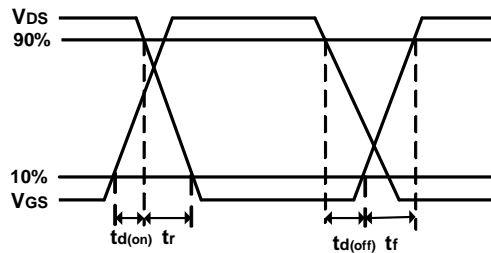
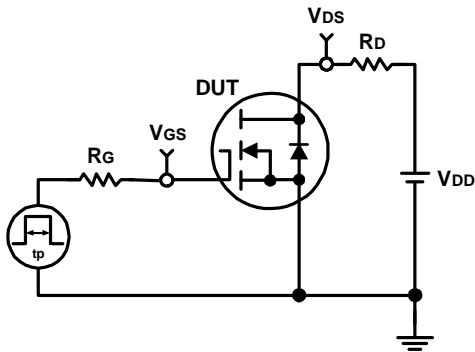
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms

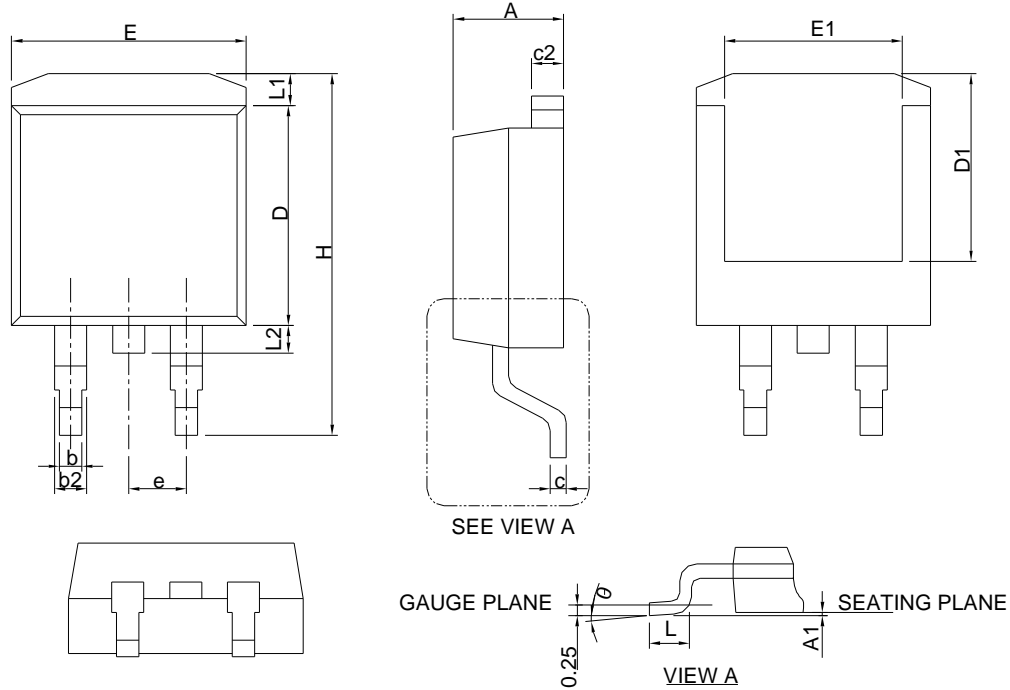


Switching Time Test Circuit and Waveforms



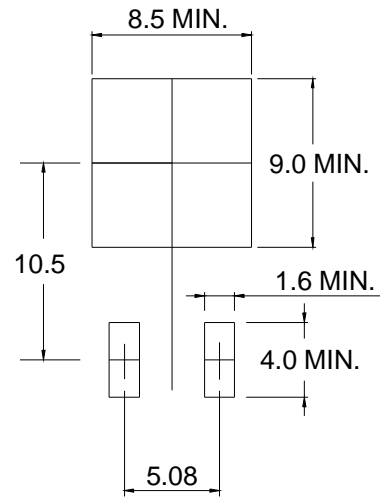
Package Information

TO-263-3



SYMBOL	TO-263-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b2	1.14	1.78	0.045	0.070
c	0.38	0.74	0.015	0.029
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380
D1	6.00	9.00	0.236	0.354
E	9.65	11.43	0.380	0.450
E1	6.22	9.00	0.245	0.354
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.68	-	0.066
L2	-	1.78	-	0.070
θ	0°	8°	0°	8°

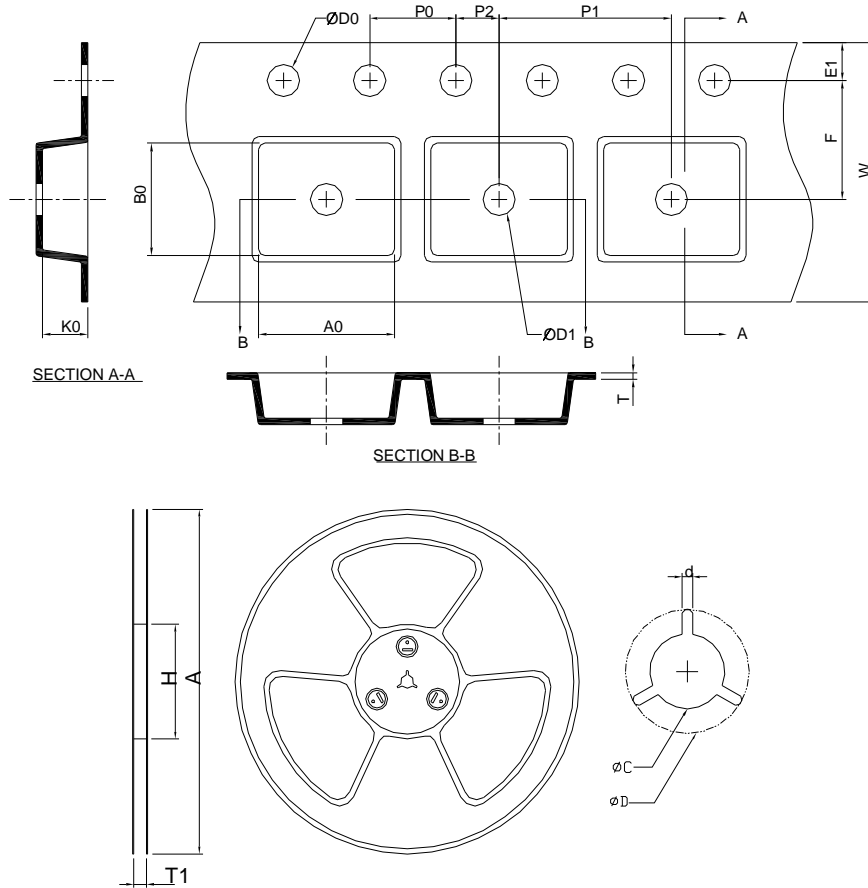
RECOMMENDED LAND PATTERN



UNIT: mm

Note : Follow JEDEC TO-263 AB.

Carrier Tape & Reel Dimensions

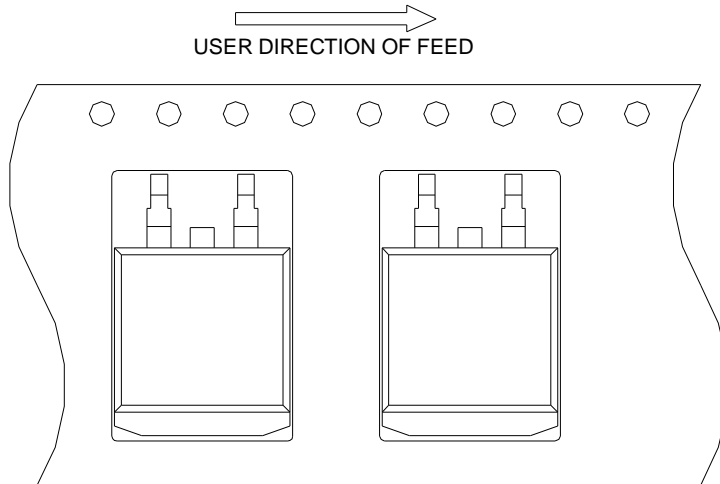


Application	A	H	T1	C	d	D	W	E1	F
TO-263-3	330.0±2.00	50 MIN.	24.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	24.0±0.30	1.75±0.10	11.5±0.10
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	16.0±0.10	2.0±0.10	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	10.8±0.20	16.1±0.20	5.2±0.20

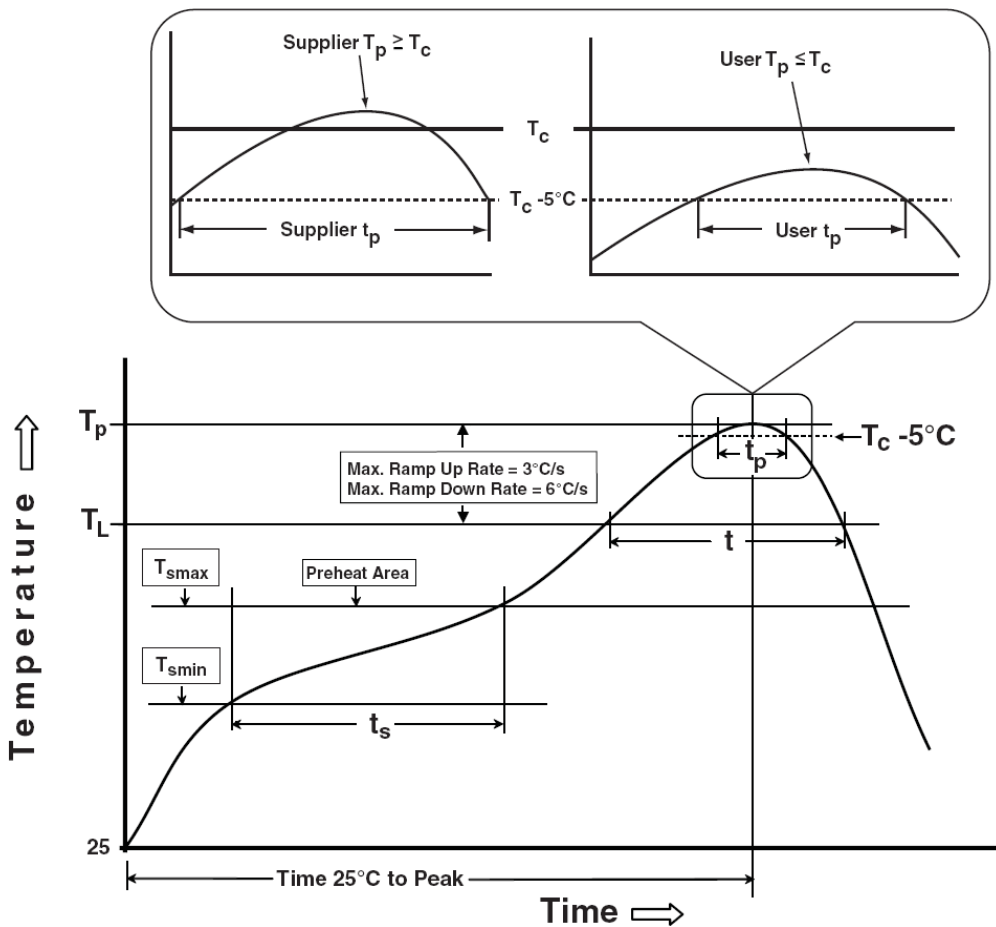
(mm)

Taping Direction Information

TO-263-3



Classification Profile



Disclaimer

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Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

Sinopower Semiconductor, Inc.

5F, No. 6, Dusing 1St Rd., Hsinchu Science Park,

Hsinchu, 30078, Taiwan

TEL: 886-3-5635818 Fax: 886-3-5642050